Heterostructured thin LaFeO$_3$/g-C$_3$N$_4$ films for efficient photoelectrochemical hydrogen evolution

Vincent Guigoz, Lavinia Balan, Abdelhay Aboulaich, Raphaël Schneider, Thomas Gries

To cite this version:

HAL Id: hal-02884612
https://hal.univ-lorraine.fr/hal-02884612
Submitted on 3 Dec 2020

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L’archive ouverte pluridisciplinaire HAL, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d’enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.
Heterostructured thin LaFeO$_3$/g-$C_3$N$_4$ films for efficient photoelectrochemical hydrogen evolution

Vincent Guigoz $^{a,b}$, Lavinia Balan $^c$, Abdelhay Aboulaich $^d$, Raphaël Schneider $^{a,*}$, Thomas Gries $^{b,*}$

$^a$ Université de Lorraine, CNRS, LRGP, F-54000 Nancy, France

$^b$ Université de Lorraine, CNRS, IJL, F-54000 Nancy, France

$^c$ CEMHTI-UPR 3079 CNRS, Site Haute Température, 1D avenue de la Recherche Scientifique, 45071 Orléans, France

$^d$ Université Clermont Auvergne, Institut de Chimie de Clermont Ferrand UMR 6296 CNRS/UBP/Sigma Clermont, Campus des Cézeaux, TSA 60026-CS 60026, 63178, AUBIERE Cedex, France

* Corresponding authors.

E-mail addresses: raphael.schneider@univ-lorraine.fr; thomas.gries@univ-lorraine.fr

Abstract

The deposition of LaFeO$_3$ at the surface of a graphitic carbon nitride (g-$C_3$N$_4$) film via magnetron sputtering followed by oxidation for photoelectrochemical (PEC) water splitting is reported. The LaFeO$_3$/g-$C_3$N$_4$ film was investigated by various characterization techniques including SEM, XRD, Raman spectroscopy, XPS and photo-electrochemical measurements. Our results show that the hydrogen production rate of a g-$C_3$N$_4$ film covered by a LaFeO$_3$ film, exhibiting both a thickness of ca. 50 nm, is of 10.8 μmol.h$^{-1}$.cm$^{-2}$ under visible light irradiation. This value is ca. 70% higher than that measured for pure LaFeO$_3$ and g-$C_3$N$_4$ films.
and confirms the effective separation of electron-hole pairs at the interface of LaFeO$_3$/g-C$_3$N$_4$ films. Moreover, the LaFeO$_3$/g-C$_3$N$_4$ films were demonstrated to be stable and retained a high activity (ca. 70%) after the third reuse.

**Keywords**

Lanthanum ferrite; graphitic carbon nitride; photoelectrochemical water splitting; hydrogen evolution

**Introduction**

Hydrogen (H$_2$) is a clean and carbon-free burning molecule and has become a promising candidate fuel as future energy carrier due to high energy density [1,2]. However, 96% of H$_2$ worldwide production originates from fossil fuels [3], which poses several environmental concerns such as the emission of a large amount of greenhouse gases such as CO$_2$, SOx, NOx and CO as by-products, which are mainly responsible of global warming issue. In addition to its environmental issues, most of H$_2$ production methods are highly energy consuming, which limits their application at very large scale. A big achievement would be to produce H$_2$ via an environmental-friendly and cost-effective method. In this regard, solar energy can be converted into H$_2$ by splitting water into oxygen (O$_2$) and H$_2$, storing the solar energy in the H-H chemical bond (artificial photosynthesis). Hydrogen photoproduction can be achieved by two means, photocatalytically via the irradiation of a catalyst in water or photoelectrochemically at the surface of a semiconductor electrode in three-electrodes cells in which the illuminated semiconductor electrode either oxidizes water into O$_2$ (photoanode) or reduces it into H$_2$ (photocathode) [4,5]. This photoelectrode is connected to a counter electrode that electrocatalyzes the respective half redox reaction.

Fujishima and Honda first demonstrated photoelectrochemical (PEC) water splitting for hydrogen production with a biased photoanode (titanium oxide, TiO$_2$) in 1972 [6]. To produce H$_2$ using PEC, the semiconductor material (photoelectrode) should have a suitable bandgap for water splitting half reactions to occur, absorb in the visible region of the solar spectrum, a high quantum efficiency (i.e. produce reactive charge carriers per absorbed photon) and a good photochemical stability (i.e. withstand photocorrosion) [7-10]. To reduce
costs and environmental impact, the chosen material should also be abundant and non-toxic.

Most water splitting studies were conducted using wide bandgap semiconductors like TiO$_2$ or ZnO that can only be activated by UV light [11,12]. In recent years, intensive efforts were devoted to the extension of TiO$_2$ or ZnO visible light absorption and to the improvement of their photocatalytic properties via doping or building heterostructured catalysts in which the separation of charge carriers is improved [13–15].

Recently, lanthanum ferrite perovskite (LaFeO$_3$) has attracted a great attention [16-21], with applications in sensors [22], catalysts [23] and monitoring [24] due to its good chemical and thermal stability and its low toxicity. Moreover, LaFeO$_3$ has an advantageous optical bandgap, up to 2.1 eV, allowing the absorption of visible light until 590 nm. However, the photocatalytic activity of pure LaFeO$_3$ and its PEC performances are modest due to the fast recombination of photogenerated electron/hole pairs, to its weak charge collection, and to its low specific surface area [16,25–30]. Noteworthy is also that LaFeO$_3$ exhibits poor or no activity for H$_2$ photoproduction because its conduction band (CB) edge is close and too positive compared to that of the H$^+/\text{H}_2$ couple (0 V), which does not allow photogenerated electrons to reduce H$^+$ into H$_2$.

Heterostructured catalysts associating LaFeO$_3$ to reduced graphene oxide [31], TiO$_2$ [32,33] or graphitic carbon nitride (g-C$_3$N$_4$) [34-41] have received a much higher interest due to the improved separation of charge carriers. The organic g-C$_3$N$_4$ semiconductor is a highly promising material for photocatalytic applications like H$_2$ production, environmental remediation or CO$_2$ reduction into fuel molecules due to its low cost, its high thermal and chemical stability and its relatively low bandgap of ca. 2.7 eV allowing the absorption of visible light up to 460 nm [42-46]. Moreover, the energy positions of g-C$_3$N$_4$ valence band (VB) and of its CB are located at ca. 1.4 and -1.3 eV vs normal hydrogen electrode (NHE), making this semiconductor suitable for water splitting [42–45]. As LaFeO$_3$, g-C$_3$N$_4$ suffers from various drawbacks like a high recombination rate of charge carriers and a low charge mobility. Due to the adequate band edge positions of g-C$_3$N$_4$ and LaFeO$_3$, the coupling of these materials affords a Z-scheme charge transfer system which allows to promote the separation of electron/hole pairs and to extend the visible light absorption [30,34–41]. Xu et al. reported the preparation of a visible light active LaFeO$_3$ (5%)/g-C$_3$N$_4$ photocatalyst via a
calcination process [34]. After association to 2% NiS used as co-catalyst and using triethanolamine as sacrificial substrate, a H₂ evolution rate (HER) of 121 µmol.g⁻¹.h⁻¹ was obtained. Acharya et al. also described the mechanical synthesis of a LaFeO₃ (80%)/g-C₃N₄ catalyst exhibiting a HER of 1152 µmol.g⁻¹.h⁻¹ using methanol as sacrificial substrate and 1% Pt as co-catalyst [41].

Herein, we report the first preparation of a thin LaFeO₃ film deposited on a g-C₃N₄ film for PEC water splitting. Spin-coating and magnetron sputtering, which are facile and scalable methods, were used to deposit g-C₃N₄ and LaFeO₃, respectively, to obtain heterostructured films. Photocurrent and HER measurements revealed that photocatalytic properties of LaFeO₃ were significantly improved after coupling with g-C₃N₄. A high HER value of 10.8 µmol⁻¹.h⁻¹.cm⁻² was determined after 7 h under visible light irradiation. Moreover, 70% of the photocatalytic activity of the LaFeO₃/g-C₃N₄ were retained after the third cycle, indicating its good stability.

**Experimental section**

**Synthesis and deposition of g-C₃N₄ on FTO**

The g-C₃N₄ powder was synthesized by heat treatment of urea. Briefly, urea was placed in a crucible and stepwise heated at 250, 350 and 450°C for 1 h each with a heating rate of 10°C.min⁻¹. After cooling to room temperature, the pale yellow solid was grounded into powder.

Prior to any deposition, a transparent conductive oxide substrate, Fluorine doped Tin Oxide coated glass (FTO, TEC 7 Ω/sq, Solems) was successively washed with acetone and ethanol for ten minutes in an ultrasonic bath before drying with compressed air. g-C₃N₄ was dispersed in methanol at the concentration of 0.5 mg·mL⁻¹ and ultrasonicated for 20 min. The dispersion was then left to rest for at least 4 days to let the largest particles to sediment. The concentration of the remaining lightweight exfoliated g-C₃N₄ in methanol was determined to be of ca. 0.10 mg·mL⁻¹. The dispersion was stable for months.
g-C$_3$N$_4$ nanosheets were deposited by dropping 10 µL of the previously prepared dispersion solution onto cleaned FTO and rotated at 500 rpm for 10 s. This step was repeated several times in order to control the g-C$_3$N$_4$ film thickness. Spin-coating was followed by a thermal treatment at 115°C on a hot plate for 30 min in air to evaporate methanol and assure good electrical contact.

**Elaboration of LaFeO$_3$ thin film**

LaFe films were deposited on pre-cleaned FTO or on g-C$_3$N$_4$ deposited on FTO by DC magnetron co-sputtering from two metallic targets: iron target (diameter: 50 mm, thickness: 0.25 mm, purity: 99.5%) and lanthanum target (diameter: 50 mm, thickness: 3 mm, purity: 99.9%). Two independent magnetrons focused at the centre of the substrate-holder and inclined by 30° with respect to the substrate normal were used with a target to substrate distance set equal to 10 cm. The base pressure in the sputtering chamber during deposition was 0.58 Pa in an atmosphere containing 10 vol.% H$_2$ – 90 vol.% Ar. The compositions of the thin films were controlled by the adjustment of the power applied to metallic target and stoichiometric LaFe films were obtained at 80 W on Fe target and 65 W on La target, respectively. Before deposition, a shutter was placed in front of the target to isolate the substrate during 5 min in order to remove native oxide layers. Thickness was controlled by adjusting the sputtering time. The substrate-holder rotated at 28 rpm during deposition to ensure homogeneity. Thin films were deposited without external heating and the deposition temperatures were below 50°C. At these temperatures, films remained amorphous and a post-annealing was performed to synthesize LaFeO$_3$ perovskite structure in a tubular furnace at 500°C for 2 h in air.

**Characterization**

The surface morphology of the films was imaged by a Philips XL30S-FEG scanning electron microscope (SEM). Film thicknesses were measured by SEM cross-section observation. The La/Fe atomic ratio was determined by energy dispersive spectroscopy (EDS). The crystallographic structure of the films was determined by X-ray diffraction (XRD) performed at room temperature using Bragg-Brentano θ/2θ measurements on a D8 Advance Bruker
diffractometer (Cu Kα, λ = 1.54056 Å). Fourier transform infrared (FT-IR) spectra were recorded on an Agilent Cary 680 equipped with an attenuated total reflection (ATR) element (resolution = 4 cm⁻¹). UV-visible absorption spectra were recorded on Cary 7000 UMS Agilent UV-visible spectrophotometer. Raman analyses were conducted using a Horiba Labram HR800 equipment with a 633 nm laser. All the optical measurements were performed at room temperature under ambient conditions.

X-ray photoelectron spectroscopy (XPS) analyses were performed on a Gammasdata Scienta (Uppsala, Sweden) SES 200-2 spectrometer under ultra-high vacuum (P < 10⁻⁹ mbar). The measurements were performed at normal incidence (the sample plane is perpendicular to the emission angle). The spectrometer resolution at the Fermi level is about 0.4 eV. The depth analyzed extends up to about 8 nm. The monochromatized Al Kα source (1486.6 eV) was operated at a power of 420 W (30 mA and 14 kV) and the spectra were acquired at a take-off angle of 90° (angle between the sample surface and photoemission direction). During acquisition, the pass energy was set to 500 eV for wide scans and to 100 eV for high-resolution spectra. CASAXPS software (Casa Software Ltd, Teignmouth, UK, www.casaxps.com) was used for all peak fitting procedures and the areas of each component were modified according to classical Scofield sensitivity factors.

The photoelectrochemical performance of as-prepared samples was measured in a three-electrode cell with Pt wire as the counter electrode, a saturated Ag/AgCl electrode as reference electrode and FTO glass coated with LaFeO₃ or LaFeO₃/g-C₃N₄ materials with a surface area of 1 cm² as the working electrode. A 0.1 M Na₂SO₄ (pH = 7) aqueous solution was used as electrolyte. All measurements were carried out under light illumination of 1 sun (100 mW·cm⁻²) provided by a 300 W Xe arc lamp fitted with an AM 1.5G filter. Linear sweep voltammetry (LSV) measurements were performed by scanning the potential from -0.8 V to 0 V vs Ag/AgCl at a scan rate of 5 mV.s⁻¹. Chronoamperometric measurements were recorded at a constant potential of -0.30 V vs the reference electrode by using a SP150 BioLogic potentiostat, cycling between dark and light illuminations of 30 s each for 10 min for evaluating photocurrent density.

Electrochemical Impedance spectroscopy (EIS) was performed for Nyquist measurements. Frequency range of 500 kHz - 1 mHz and magnitude of the modulation signal of 10 mV were used. Applied potential was -0.3 V vs Ag/AgCl under 1 sun illumination. Mott-Schottky
spectra were acquired at frequencies from 6 kHz to 10 kHz in the potential range of 0.6 V to 1.6 V vs the reference electrode in the dark.

**Hydrogen photoproduction**

The photocatalytic hydrogen production test was performed in a sealed custom-made metallic photoelectrochemical cell with an attached quartz viewport using the irradiation conditions previously described. The whole system was filled with 0.1 M Na₂SO₄ (pH = 7) and purged with argon for 1 h before measurements. During the reaction, the amount of produced H₂ was determined with online quadrupole mass spectrometer (MS, Inficon Transpector MPS 100) operating with Ar as carrier gas. Measurements were realized at an interval of 1 h and averaged over 2 min.

**Results and discussion**

**Materials characterization**

LaFeO₃/g-C₃N₄ films on FTO were prepared using a three steps process depicted in Fig. 1. First, exfoliated g-C₃N₄ was coated on FTO via spin-coating. Next, La and Fe were deposited at the surface of g-C₃N₄ by DC magnetron co-sputtering. Finally, crystalline LaFeO₃ was produced by air oxidation of La-Fe films at 500°C for 2 h.

**Fig. 1.** Schematic illustration of the LaFeO₃/g-C₃N₄ film synthesis on FTO.

In order to reveal the structure, the composition and the morphology of the prepared samples, SEM, FT-IR, XRD and XPS analyses were conducted. Due to the high roughness of the FTO support, g-C₃N₄ and LaFeO₃ layers could not be observed by SEM (Fig. S1 and 2). The
associated EDS mappings (Fig. 2) show that g-C₃N₄ and LaFeO₃/g-C₃N₄ films are homogeneously distributed at the surface of FTO. The La/Fe ratio in La-Fe and LaFeO₃ films is of ca. 1.0 and the La/Fe/O ratio in the LaFeO₃ film is of 1.0/1.0/3.0 (Fig. S2), which indicates the successful deposition of the LaFeO₃ film at the surface of g-C₃N₄. When the same deposition process was conducted on Si instead of FTO, thicknesses of 50 and 100 nm could be determined by SEM for g-C₃N₄ and LaFeO₃ layers (Fig. S3), respectively, which further confirms the efficiency of the magnetron co-sputtering method for the preparation of hierarchically structured films.

![Fig. 2.](image-url)

**Fig. 2.** (a) SEM image of LaFeO₃/g-C₃N₄ on FTO and EDS elemental mapping of (b) C, (c) N, (d) La, (e) Fe and (f) O.

Fig. 3a shows the FT-IR spectra of pure g-C₃N₄ and of LaFeO₃/g-C₃N₄ on the FTO surface. For g-C₃N₄, the bands observed between 1625 and 1200 cm⁻¹ can be ascribed to C-N and C=N bonds stretching vibrations while signals appearing at 1250 and 1205 cm⁻¹ correspond to the C-NH-C stretching vibration between heptazine units [44,49]. The sharp signal located at 810 cm⁻¹ corresponds to the bending vibration of triazine units [46-50]. The peaks of g-C₃N₄ disappear after deposition of LaFeO₃. The signal at 541 cm⁻¹ is the characteristic stretching vibration of the Fe-O bond in the octahedral FeO₆ of crystalline LaFeO₃ [51]. The two signals observed at 1469 and 1406 cm⁻¹ can be attributed to the splitting of the ν₃ asymmetric stretching of La or Fe carbonates present at the surface of the film [52].
The powdered g-C₃N₄ shows a characteristic peak at 2θ = 26.5° corresponding to the (002) plane and associated to the interlayer stacking of the conjugated aromatic systems (interlayer distance (d) of 0.32 nm) (Fig. 3b) [53]. The intensity of the g-C₃N₄ peak after deposition via spin coating on FTO is low compared to the signals of the substrate due to the weak amount of g-C₃N₄ present at the FTO surface (estimated to be ca. 1 µg per cm²). The thickness of the g-C₃N₄ layer is of ca. 50 nm compared to the 600 nm thickness of FTO. The signal of g-C₃N₄ can be better observed after deposition on a Si substrate (Fig. S4). Finally, the peaks of LaFeO₃ deposited on g-C₃N₄ can be indexed to the orthorhombic structure (JCPDS No 00-037-1493) [54]. The co-existence of the peaks related to LaFeO₃ and g-C₃N₄ confirms the presence of these two materials on the FTO substrate and indicates that the g-C₃N₄ layer is stable after the oxidative treatment following the deposition of La and Fe by magnetron co-sputtering.

Raman spectroscopy was also used to examine the structural phase of the materials prepared (Fig. 3c). For pure LaFeO₃, La vibrations can be observed below 200 cm⁻¹ while signals observed at 301 and 433 cm⁻¹ correspond to Aᵣ and B₃g modes, respectively. These values are in good agreement with those described in the literature for the orthorhombic structure of LaFeO₃ [26]. The other peaks observed may originate from structural defects (cation or oxygen vacancies). The strong signal appearing at 625 cm⁻¹ likely originates from two-phonon scattering and/or impurities as previously reported [55]. After deposition of LaFeO₃ on g-C₃N₄, signals corresponding to CN heterocycles appear in the Raman spectrum [56], further confirming the successful association of g-C₃N₄ with LaFeO₃.
Fig. 3. (a) FT-IR spectra of g-C₃N₄ and of LaFeO₃/g-C₃N₄ deposited on FTO,
(b) XRD patterns of g-C₃N₄, FTO, g-C₃N₄ on FTO and LaFeO₃/g-C₃N₄ on FTO and (c) Raman
The surface chemical composition and the oxidation states of the elements in the LaFeO$_3$/g-C$_3$N$_4$ film were characterized by XPS (Fig. 4 and Fig. S5). The XPS survey spectrum of the film shows only the presence of La, Fe, O and C elements. The signal of N 1s could not be detected due to the thick layer of LaFeO$_3$ at the surface of g-C$_3$N$_4$ (the penetration depth of XPS, ca. 10 nm, does not allow reaching the g-C$_3$N$_4$ layer). The peaks of Fe 2p$_{3/2}$ and Fe 2p$_{5/2}$ are located at 711.60 and 724.02 eV, respectively, values corresponding to the core level spectra of Fe$^{3+}$ cations included in an oxide (Fig. 4a) [28,41]. The high resolution XPS spectrum of La 3d shows signals at 855.40 and 838.59 eV corresponding to the spin-orbit splitting of La 3d$_{3/2}$ and La 3d$_{5/2}$ (Fig. 4b) [41,57]. The binding energies also confirm that La is present in the +3 oxidation state and incorporated in an oxide. The O 1s peak can be deconvoluted into two signals located at 529.68 and 531.65 eV which can be attributed to O atoms in the LaFeO$_3$ crystal lattice (La-O and Fe-O bonds) and to chemisorbed O containing species at the surface of LaFeO$_3$, respectively (Fig. 4c). Finally, the three peaks located at 285.0, 286.60 and 289.02 eV likely originate from carbon contaminants located at the surface of the LaFeO$_3$/g-C$_3$N$_4$ film (Fig. 4d).
Fig. 4. High resolution XPS spectra of (a) Fe 2p, (b) La 3d, (c) O 1s and (d) C 1s for the LaFeO$_3$/g-C$_3$N$_4$ film.

Optical and electrochemical measurements

The UV-visible absorption spectrum of the pure 50 nm-thick LaFeO$_3$ film is presented in Fig. 5a. The optical bandgap (E$_g$) was determined using the Tauc/David-Mott model, by plotting ($\alpha$hv)$^{1/n}$ vs. hv, where h is Planck’s constant, $\alpha$ is the absorption coefficient, $\gamma$ is the photon frequency and n is 1/2 for direct allowed transitions or 2 for indirect allowed transition [58]. The E$_g$ value was estimated by extrapolating the linear region of the plot onto energy axis (insets of Fig. 5a). The absorption spectrum clearly shows two absorption edges, located at approximately $\lambda_1 = 350$ nm and $\lambda_2 = 480$ nm. The optical properties of LaFeO$_3$ were studied by Scafetta et al. using the density functional theory (DFT) [59]. The lowest bandgap was demonstrated to originate from a direct forbidden transition. Applying the same model to the present experimental data, a bandgap of ca. 2.28 eV was determined. This value is in
good agreement with those described in the literature for nanocristalline LaFeO$_3$ [59,60]. A similar approach was also been used to determine the higher indirect transition at ca. 3 eV. The high absorption in the visible region originating from the electronic transition from the valence band to the conduction band (O 2p $\rightarrow$ Fe 3d) [17] should be beneficial for the photocatalytic activity under simulated solar light irradiation. Similar optical features were observed for the LaFeO$_3$ film deposited on g-C$_{3}$N$_{4}$ (Fig. 5b).

**Fig. 5.** UV-visible optical absorption spectrum of (a) a 50 nm-thick LaFeO$_3$ film on FTO (the insets show the Tauc plots for a direct-forbidden and indirect-allowed model for the first and second transitions, respectively). (b) LaFeO$_3$/g-C$_3$N$_4$ film.
Electrochemical impedance spectroscopy (EIS) measurements were conducted to determine the LaFeO$_3$ flatband potential. Fig. 6 shows the Mott-Schottky plots for LaFeO$_3$ thin film at different frequencies in the dark. The negative slope indicates that LaFeO$_3$ behaves as a p-type semiconductor. The flatband potential was estimated using the following Mott-Schottky equation for p-type semiconductor [61]:

$$\left(\frac{1}{C}\right)^2 = \frac{2}{\varepsilon_r \varepsilon_0 \epsilon N_D} (V - V_{fb} - \frac{k_B T}{e})$$

where $C$ is the capacitance, $e$ is the electronic charge, $\varepsilon_r$ is the relative permittivity of materials, $\varepsilon_0$ is the permittivity of vacuum, $N_D$ is the carrier concentration, $k_B$ is the Boltzmann’s constant, $T$ is the absolute temperature, $A$ is the area of electrode, $V$ is the applied potential and $V_{fb}$ is the flatband potential. Therefore, the flatband potential can be obtained by extrapolating the linear portion of the Mott-Schottky plot to V axis. A similar potential of +1.47 V vs Ag/AgCl was obtained for each applied frequency. The measured flatband potential can be converted to the RHE scale using the Nernst equation:

$$V_{RHE} = V_{Ag/AgCl} + 0.197 + 0.059 \cdot pH$$

and was determined to be 2.08 V vs NHE.
Fig. 6. Mott-Schottky plots for LaFeO$_3$ film (50 nm) at different frequencies determined from EIS measurements in the dark, in Na$_2$SO$_4$ (pH = 7).

Assuming in first approximation that the flatband potential of a p-type semiconductor is very close to the valence band (VB) edge position [52], the valence band maximum (VBM) of LaFeO$_3$ was estimated to be 2.08 V vs RHE. Combined with the bandgap of 2.28 eV, the conduction band minimum (CBM) of the LaFeO$_3$ film was estimated to be -0.2 V vs RHE. As the accuracy of the flatband value determined from Mott-Schottky plot may be debatable due to a possible influence of the surface roughness and the electrolyte [62], a semi-empirical method was also used to confirm the band positions. CBM and VBM values were calculated from Mulliken’s electronegativity at point of zero charge using the following equation [63]:

$$E_{VB} = \chi - E^e + 0.5E_g \quad (3)$$

$$E_{CB} = E_{VB} - E_g \quad (4)$$

where $E_{VB}$ and $E_{CB}$ are the VB edge potential and CB edge potential respectively, $\chi$ is the absolute electronegativity of the semiconductor on Mulliken’s scale ($\chi = 5.54$ for LaFeO$_3$), $E^e$ is the energy of free electrons on the hydrogen scale (4.5 eV vs RHE) and $E_g$ is the bandgap energy estimated from UV-Vis absorption spectra. VBM and CBM positions were estimated.
to be 2.18 and -0.1 V vs RHE, respectively. These theoretical calculations are in good agreement with Mott-Schottky plots.

VBM and CBM positions of g-C$_3$N$_4$ were determined in [47]. The corresponding energy diagram of LaFeO$_3$ and g-C$_3$N$_4$ before contact is reported in Fig. 7a. LaFeO$_3$ exhibits VBM and CBM that straddle the redox potential of water. This suggests that LaFeO$_3$ is able to generate hydrogen using visible part of the spectrum without applying any external bias voltage as observed by Pawar et al. [20]. However, the kinetics of production is very low due to the very close position of CB in regards to reduction potential of hydrogen. LaFeO$_3$ associated to g-C$_3$N$_4$ will form a p-n heterojunction. PEC efficiency can be greatly influenced by the recombination rate of photo-generated charge carriers and p-n junctions generally promote the effective separation of light-induced electrons and holes. Before contact, CB and Fermi level positions of LaFeO$_3$ are lower than those of g-C$_3$N$_4$. At the junction, the Fermi level after contact, under equilibrium conditions, is equal and constant in g-C$_3$N$_4$ and LaFeO$_3$, causing an energy band bending. Indeed, after contact between p-type LaFeO$_3$ and n-type g-C$_3$N$_4$, electrons diffuse from g-C$_3$N$_4$ to LaFeO$_3$ due to the initial positions of CB, leading to an accumulation of negative charges in LaFeO$_3$ close to the junction. At the same time, a positive section in g-C$_3$N$_4$ is generated near the junction. As a consequence, the Fermi level and energy band positions of g-C$_3$N$_4$ shift downward (to more positive potentials), while those of LaFeO$_3$ shift upward (to more negative potentials) to form an equilibrium state, where an inner electric field is generated and the CB of LaFeO$_3$ is higher than that of g-C$_3$N$_4$ (Fig. 7b). Thus, photogenerated electrons on the CB of LaFeO$_3$ will transfer to that of g-C$_3$N$_4$. Migration of electrons and holes are promoted by the internal field. Subsequently, the interface of the heterojunction will improve the separation of electron-holes pairs and reduce their recombination probability [64].
Fig. 7. Schematic diagrams of band energy positions of g-C₃N₄ and LaFeO₃ (a) before contact and (b) the proposed electrons/holes transfer and separation processes after contact.

**Photoelectrochemical (PEC) analysis**

Linear sweep voltammetry (J-V) curves of LaFeO₃/g-C₃N₄ were recorded under simulated sunlight illumination (100 mW·cm⁻², AM 1.5G), where a chopped beam was used for acquiring both dark current and photocurrent in a single scan at a rate of 5 mV.s⁻¹ (Fig. 8a). Each cycle lasts 25 mV. The steady state photocurrent onset potential was around 0.6 V vs RHE and the dark current remained stable until 0.25 V vs RHE.

To determine the LaFeO₃ on g-C₃N₄ ratio giving the highest performance, the amount of each material was optimised from chronoamperometric tests under chopped illumination (30 s). The potential was kept constant at -0.3 V versus Ag/AgCl (0.3 V vs RHE) to ensure the minimal impact of dark current in the 0.1 M Na₂SO₄ (pH = 7) electrolyte solution. The photocurrent density varied with the amount of g-C₃N₄ underneath 50 nm-thick LaFeO₃ (Fig. 8b). The photoelectrode elaborated using 1 µg of g-C₃N₄ exhibits the highest photocurrent density (4 µA·cm⁻²). The thickness of the LaFeO₃ film deposited on 1 µg of g-C₃N₄ was also found to affect the photocurrent density (Fig. 8c).
Optimal quantities for both materials were thus determined to be a 50 nm thick layer of LaFeO$_3$ deposited on top of 1 µg of g-C$_3$N$_4$ with a maximum photocurrent density of 4 µA.cm$^{-2}$. Spikes and transient photocurrent observed during each period can be attributed to charge carriers recombination. A large number of photoinduced electrons cannot reach the electrolyte before recombining with holes. The photocurrent density becomes stable only when the balance between charge generation, separation, transport and recombination processes is achieved. As expected, thickness of photoelectrode is major parameter that directly impacts the photocurrent density. The electron transport within LaFeO$_3$ is low and charge carriers recombination probability increases with thickness. By contrast, photoactive materials have to be thick enough to ensure light absorption leading to the formation of a high density of electron/hole pairs [65]. The observed higher photocurrent density of LaFeO$_3$/g-C$_3$N$_4$ by comparison with LaFeO$_3$ suggests an enhanced charge carriers separation in the heterostructured photoelectrode. Fig. 8d shows the Nyquist plots of EIS spectra for LaFeO$_3$ (50 nm) and optimised LaFeO$_3$/g-C$_3$N$_4$ under illumination. The semicircle diameter is related to the charge transfer resistance at the electrode/electrolyte interface. LaFeO$_3$/g-C$_3$N$_4$ has a smaller arc diameter than that of LaFeO$_3$, which means a smaller charge transfer resistance. Both photocurrent and EIS results indicate that heterostructured LaFeO$_3$/g-C$_3$N$_4$ film exhibits more efficient electron-hole separation under simulated sunlight illumination, mainly due to the electrostatic field in the junction [66].
Fig. 8. Current-potential curve (a) and current-time curves of LaFeO$_3$/g-C$_3$N$_4$ heterojunctions at $-0.3$ V vs Ag/AgCl as a function of (b) the quantity of g-C$_3$N$_4$ spin-coated on FTO (LaFeO$_3$ thickness = 50 nm) and (c) the LaFeO$_3$ film thickness (amount of g-C$_3$N$_4$ = 1 µg) under chopped illumination. (d) EIS Nyquist plots of 50 nm thick LaFeO$_3$ and optimised LaFeO$_3$/g-C$_3$N$_4$ heterostructure (electrolyte: 0.1 M Na$_2$SO$_4$ (pH = 7)).

The stability is a crucial parameter to determine if a system is suitable for practical utilisation. In order to test the stability, a chronoamperometry measurement was conducted for LaFeO$_3$/g-C$_3$N$_4$ heterostructured photocathode at a constant potential of $-0.3$ V vs Ag/AgCl over a 24 h period under a continuous simulated sunlight illumination in a 0.1 M Na$_2$SO$_4$ electrolyte solution (Fig. 9). After a slight drop in the first 2 h, the current density remained almost constant over the following 22 h (ca. 2.9 µA.cm$^{-2}$), confirming excellent stability of the photoelectrode. The slight decrease of photocurrent at the beginning of the reaction is generally attributed to the accumulation of gas bubbles at the electrode/electrolyte interface leading to a reduced effective surface area [67]. LaFeO$_3$ and g-C$_3$N$_4$ are promising photoelectrode materials mainly due to their chemical and thermal stability. Moreover, LaFeO$_3$ thin films synthesized by magnetron sputtering have a dense
columnar structure with no voids and pores. As a consequence, the electrolyte cannot deeply penetrate in the film and the effective surface area is low, leading to a relatively low photocurrent density. However, the compact nature of the films ensures a good stability of the photoelectrodes by limiting their degradation during a long period of operation. LaFeO$_3$/g-C$_3$N$_4$ heterostructured films can thus be used as photocathode for hydrogen production performed over several hours.

**Fig. 9.** J-t plot at -0.3V vs Ag/AgCl of 50 nm LaFeO$_3$ deposited over 1 µg of g-C$_3$N$_4$, insert is a detail of the first hour.

**Hydrogen evolution measurement**

Fig. 10a shows the hydrogen production rates of electrodes composed of g-C$_3$N$_4$, LaFeO$_3$ and optimized LaFeO$_3$/g-C$_3$N$_4$ in an aqueous Na$_2$SO$_4$ (pH = 7) electrolyte under a continuous simulated sunlight illumination and at a constant potential of -0.3 V vs Ag/AgCl. The hydrogen production rate was monitored each hour (over 7 h) by mass spectrometry. The cell was first purged with argon for 1 h to ensure that oxygen from air was not involved when the reaction starts. It is worth noting that hydrogen production rates generated by these different photocathodes are in good agreement with current-potential curves. Samples showed very similar hydrogen evolution rates with an initial activation period of
about 3 h, followed by a stable and maximum production period. H₂ production rates of g-C₃N₄, LaFeO₃ and LaFeO₃/g-C₃N₄ in the steady states are 5.5, 6.2 and 10.8 µmol.h⁻¹.cm⁻², respectively. As a consequence, an increase of 74% in H₂ production rate is observed by depositing a g-C₃N₄ sublayer underneath LaFeO₃ thin film. To determine the stability of LaFeO₃/g-C₃N₄ heterostructured film, sample underwent 3 cycles of water splitting test (Fig. 10b). These results provide additional evidence that the film is reusable although a decrease of 30% is observed after the third cycle.

Based on the previously described experimental results, a possible mechanism can be proposed for the photogenerated charges separation and the PEC water splitting process (Fig. 10c). Under visible light irradiation, both g-C₃N₄ and LaFeO₃ absorb photons and electron-hole pairs are generated. In the heterostructured film, photo-excited electrons in the CB of g-C₃N₄ can transfer to the CB of LaFeO₃ while holes in the VB of LaFeO₃ move to the VB of g-C₃N₄, thus facilitating the separation of electron/hole pairs. In the overall PEC process, the reaction of hydroxyl anions OH⁻ (or H₂O) at the Pt counter electrode will produce electrons that can combine with holes in the VB of g-C₃N₄. Due to their more positive potential than the H⁺/H₂ couple, the electrons in the CB of LaFeO₃ can reduce H⁺ into H₂. The LaFeO₃/g-C₃N₄ photocathode benefits from the efficient charge carrier separation and exhibits a high PEC water splitting efficiency.
Fig. 10. (a) Hydrogen production rate of LaFeO$_3$, g-C$_3$N$_4$ and LaFeO$_3$/g-C$_3$N$_4$ photoelectrodes and (b) stability performances of LaFeO$_3$/g-C$_3$N$_4$ heterostructured film over 3 cycles (-0.3 V vs Ag/AgCl, 0.1 M Na$_2$SO$_4$, 100 mW.cm$^{-2}$ – AM1.5G) and (c) Schematic illustration of the electron transfer pathway for visible light PEC hydrogen production using LaFeO$_3$/g-C$_3$N$_4$ films.

**Conclusion**

For the first time, a thin LaFeO$_3$ film was deposited using magnetron sputtering and associated with g-C$_3$N$_4$ for PEC hydrogen production. g-C$_3$N$_4$ was deposited directly on the substrate, prior to LaFeO$_3$, using a simple spin-coating method. Deposition of a sublayer of g-C$_3$N$_4$ improves the separation of charge carriers at the LaFeO$_3$/g-C$_3$N$_4$ interface, while optical properties of LaFeO$_3$ still allows it to absorb a large range of the visible spectra, increasing its efficiency. Optimal quantities of both materials were determined using chronoamperometry. Subsequently, water splitting test was performed to estimate the photocatalytic properties
of the g-C₃N₄/LaFeO₃ heterojunction to produce hydrogen. Associating LaFeO₃ with g-C₃N₄ led to hydrogen production rate of 10.8 µmol·h⁻¹·cm⁻² and to an increased amount of produced hydrogen by 74% compared to pure LaFeO₃. The hydrogen production remains high after three reuses, demonstrating the stability of the g-C₃N₄/LaFeO₃ film after further cycles of production and its ability to harvest light for days. Our work thus demonstrates a simple route to obtain well performant heterostructured materials systems for hydrogen production from low-cost, non-toxic and abundant components.

Acknowledgements

This work was supported partly by the French PIA project « Lorraine Université d’Excellence », reference ANR-15-IDEX-04-LUE.

Appendix A. Supplementary data

Supplementary data to this article can be found at http://doi.org/

References


May KJ, Fenning DP, Ming T, Hong WT, Lee D, Stoerzinger KA, Biegalski MD, Kolpak AM, Shao-Horn Y. Thickness-dependent photoelectrochemical water splitting on ultrathin...
